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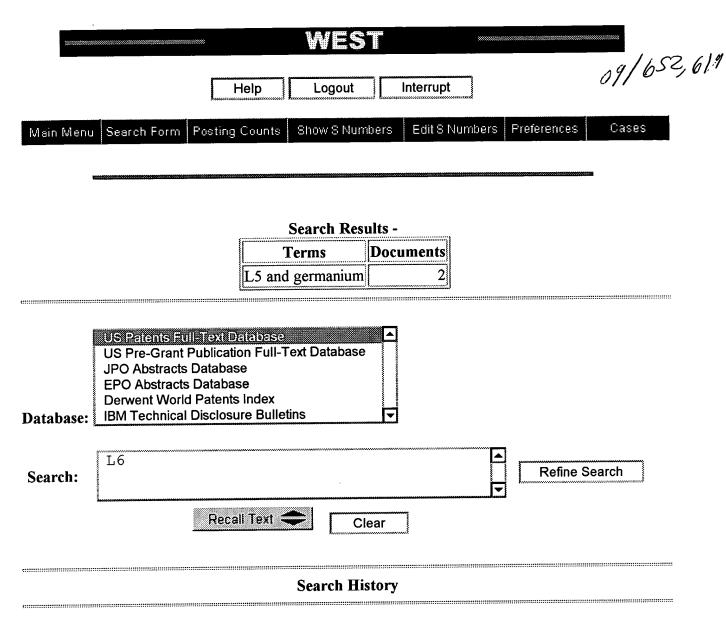
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DATE: Monday, April 08, 2002 Printable Copy Create Case

Set Name Query	Hit Count	Set Name result set
side by side		result set
DB=USPT; $PLUR=YES$; $OP=OR$		
<u>L6</u> L5 and germanium	2	<u>L6</u>
L5 L4 and (undoped near polysilicon	n) 11	<u>L5</u>
<u>L4</u> L3 and lining	162	<u>L4</u>
L3 L2 and (titanium nitride)	2947	<u>L3</u>
<u>L2</u> L1 and bpsg	3519	<u>L2</u>
<u>L1</u> integrated near circuit	167942	<u>L1</u>

END OF SEARCH HISTORY

Print Generate Collection Search Results - Record(s) 1 through 2 of 2 returned. 1. Document ID: US 6261964 B1 Jul 17, 2001 File: USPT L6: Entry 1 of 2 US-PAT-NO: 6261964 DOCUMENT-IDENTIFIER: US 6261964 B1 TITLE: Material removal method for forming a structure Full Title Citation Front Review Classification Date Reference Sequences Attachments Claims KWMC Draw. Desc Image 2. Document ID: US 6232196 B1 May 15, 2001 File: USPT, L6: Entry 2 of 2 US-PAT-NO: 6232196 DOCUMENT-IDENTIFIER: US 6232196 B1 TITLE: Method of depositing silicon with high step coverage Full Title Citation Front Review Classification Date Reference Sequences Attachments Claims KMC Draw, Desc - Image Print **Generate Collection Documents Terms** L5 and germanium

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Search Results - Record(s) 1 through 10 of 11 returned.

1. Document ID: US 6358793 B1

L5: Entry 1 of 11

File: USPT

Mar 19, 2002

US-PAT-NO: 6358793

DOCUMENT-IDENTIFIER: US 6358793 B1

TITLE: Method for localized masking for semiconductor structure

development

Full Title Citation Front Review Classification Date Reference Sequences Attachments

KMC

2. Document ID: US 6310375 B1

L5: Entry 2 of 11

File: USPT

Oct 30, 2001

US-PAT-NO: 6310375

DOCUMENT-IDENTIFIER: US 6310375 B1

TITLE: Trench capacitor with isolation collar and corresponding

manufacturing method

Full Title Citation Front Review Classification Date Reference Sequences Attachments

Draw Desc Image

KWIC

3. Document ID: US 6309975 B1

L5: Entry 3 of 11

File: USPT

Oct 30, 2001

US-PAT-NO: 6309975

DOCUMENT-IDENTIFIER: US 6309975 B1

TITLE: Methods of making implanted structures

Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments

KOMC

4. Document ID: US 6261964 B1

L5: Entry 4 of 11

File: USPT

Jul 17, 2001

US-PAT-NO: 6261964

DOCUMENT-IDENTIFIER: US 6261964 B1

TITLE: Material removal method for forming a structure

Full Title Citation Front Review Classification Date Reference Sequences Attachments KOMC Draw. Desc - Image

5. Document ID: US 6232196 B1

L5: Entry 5 of 11 File: USPT

May 15, 2001

US-PAT-NO: 6232196

DOCUMENT-IDENTIFIER: US 6232196 B1

TITLE: Method of depositing silicon with high step coverage

Full Title Citation Front Review Classification Date Reference Sequences Attachments Draws Desc Image

KOMC 1

6. Document ID: US 6048763 A

L5: Entry 6 of 11

File: USPT

Apr 11, 2000

US-PAT-NO: 6048763

DOCUMENT-IDENTIFIER: US 6048763 A

TITLE: Integrated capacitor bottom electrode with etch stop layer

Full Title Citation Front Review Classification Date Reference Sequences Attachments Draw. Desc - Image

KWIC

7. Document ID: US 6012336 A

L5: Entry 7 of 11

File: USPT

Jan 11, 2000

US-PAT-NO: 6012336

DOCUMENT-IDENTIFIER: US 6012336 A

TITLE: Capacitance pressure sensor

Full Title Citation Front Review Classification Date Reference Sequences Attachments Draw, Desc Image

8. Document ID: US 5940713 A

L5: Entry 8 of 11

File: USPT

Aug 17, 1999

US-PAT-NO: 5940713

DOCUMENT-IDENTIFIER: US 5940713 A

TITLE: Method for constructing multiple container capacitor

Full Title Citation Front Review Classification Date Reference Sequences Attachments Draw Desc Image

9. Document ID: US 5162890 A

L5: Entry 9 of 11

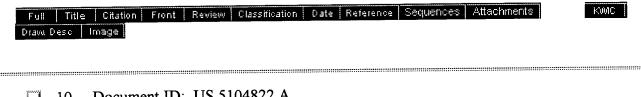
File: USPT

Nov 10, 1992

US-PAT-NO: 5162890

DOCUMENT-IDENTIFIER: US 5162890 A

TITLE: Stacked capacitor with sidewall insulation



10. Document ID: US 5104822 A

L5: Entry 10 of 11

File: USPT

Apr 14, 1992

US-PAT-NO: 5104822

DOCUMENT-IDENTIFIER: US 5104822 A

TITLE: Method for creating self-aligned, non-patterned contact

areas and stacked capacitors using the method

Full Title Citation Fro	ont Review Classification	Date Reference	Sequences	Attachments	KWIC
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☐ 11. Document ID: US 5075817 A

L5: Entry 11 of 11

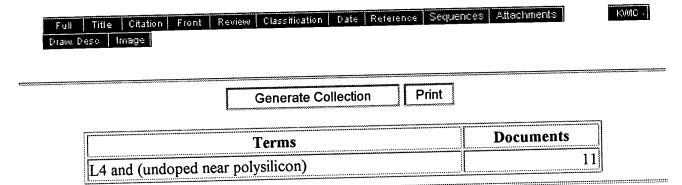
File: USPT

Dec 24, 1991

US-PAT-NO: 5075817

DOCUMENT-IDENTIFIER: US 5075817 A

TITLE: Trench capacitor for large scale integrated memory



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